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Bipolar Transistor and MOSFET Device Models

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About the eBook

Bipolar transistor and MOSFET device models is a textbook that describes basic functions and characterization models of these two types of transistors. Chapters in this text cover the fundamentals of semiconductor devices, the pn junction, high and low injection region models for bipolar transistors, and different MOSFET models such as channel doping models and gated SOI models.

Contents

- ▶ Acknowledgement
- ▶ Basics of Semiconductor Devices
- ▶ The pn Junction
- ▶ The Bipolar Transistor Model in the Low Injection Region
- ▶ The Bipolar Transistor Model in the High Injection Region
- ▶ The Fundamental MOSFET Model
- ▶ Various Channel Doping Profile MOSFET Models
- ▶ The Short Channel MOSFET Model
- ▶ The Single-Gate SOI MOSFET Model
- ▶ The Double-Gate SOI MOSFET Model
- ▶ Parasitic Limitations of MOSFETs: Gate Fringe Capacitance, Silicided Source/Drain Resistance, and Threshold Voltage Shift Due to Impurity Penetration through a Thin Gate Oxide

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